

Date:

November 9, 2005

Patent No.

6,858,307

Inventor

: Voronkov, et al

Issued

: February 22,2005

For

: METHOD FOR THE PRODUCTION OF LOW DEFECT DENSITY SILICON

Re: Request for Certificate of Correction

Consideration has been given your request for the issuance of a certificate of correction for the above-identified patent under the provisions of Rules 1.322 and 1.323.

A petition under C.F.R. 1.182 is required to correct errors in spelling or order of inventors names or addresses, since inventor's names or addresses are printed solely in accordance with the type-written names and address and in the order of the type-written names and address on the Declaration, and since the error was the result of applicant's failure to comply with the requirement that the complete and correct names and addresses in correct order be indicated on the Declaration of Oath, no correction is in order here under the provisions of Rules 1.323, unless a petition is granted.

In view of the foregoing, your request is hereby denied.

However, a petition under 37 CFR 1.182 should be directed to the attention of the Assistant Commissioner for Patents using the following mailing address or FAX number.

By Mail:

Commissioner of Patents and Trademarks

Box DAC

Washington, D.C. 20231

By Fax:

(703) 308-6916

Attn: Office of Petitions

Further correspondence concerning this matter should be filed and directed to Decisions and Certificates of Correction Branch.

RoChaun Johnson Cecelia Newman, Supervisor Decisions & Certificates of Correction Branch 703 308-9390 EXT. 119

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